

Silicon NPN Power Transistors

2N5294 2N5296 2N5298

DESCRIPTION

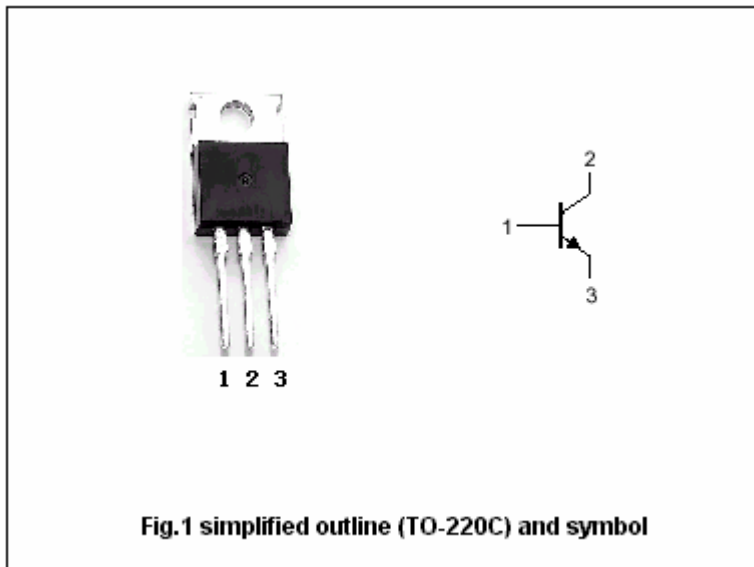
- With TO-220 package
- High power dissipation

APPLICATIONS

- Power amplifier and medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5294	80	V
		2N5296	60	
		2N5298	80	
V _{CEO}	Collector-emitter voltage	2N5294	70	V
		2N5296	40	
		2N5298	60	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		4	A
I _B	Base current		2	A
P _T	Total power dissipation	T _C =25°C	36	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	3.47	°C/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5294	70			V
		2N5296	40			
		2N5298	60			
V _{CEsat}	Collector-emitter saturation voltage	2N5294			1.0	V
		2N5296				
		2N5298				
V _{BE}	Base-emitter on voltage	2N5294			1.1	V
		2N5296			1.3	
		2N5298			1.5	
I _{CEV}	Collector cut-off current	2N5294/5298			0.5 3.0	mA
		2N5296			2.0 5.0	
I _{CER}	Collector cut-off current	2N5294/5298			0.5 2.0	mA
I _{EBO}	Emitter cut-off current	2N5294			1.0	mA
		2N5296/5298				
h _{FE}	DC current gain	2N5294	30		120	
		2N5296				
		2N5298	20		80	
f _T	Transition frequency	I _C =0.2A ; V _{CE} =4V	0.8			MHz
t _{on}	Turn-on time	2N5294			5.0	μs
		2N5296				
		2N5298				
t _{off}	Turn-off time	2N5294			15	μs
		2N5296				
		2N5298				

